

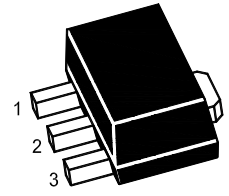
2SC4374U-AH

NPN Silicon Epitaxial Planar Transistor

for general purpose applications

Features

- AEC-Q101 Qualified and PPAP Capable
- Halogen and Antimony Free(HAF), RoHS compliant



1.Base 2.Collector 3.Emitter
SOT-89 Plastic Package

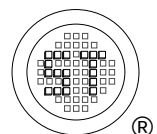
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

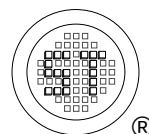
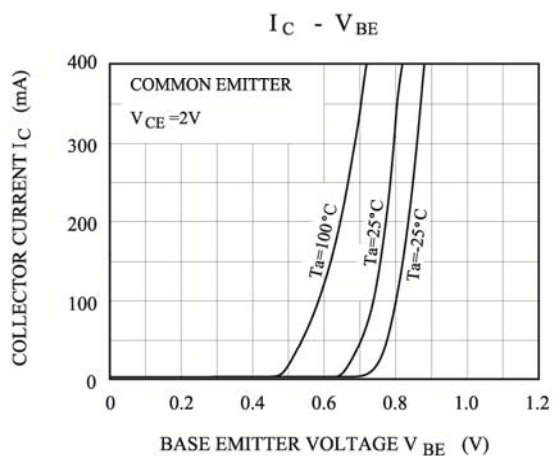
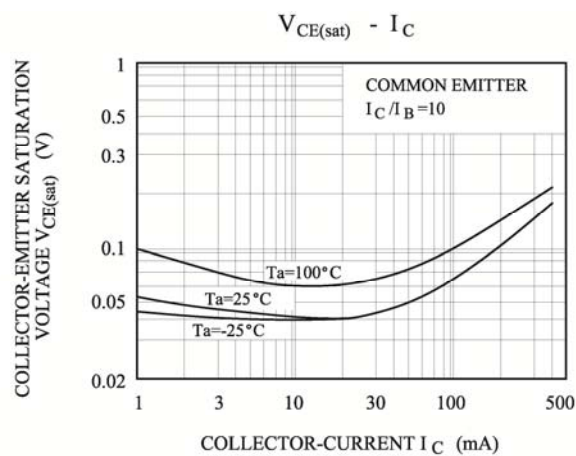
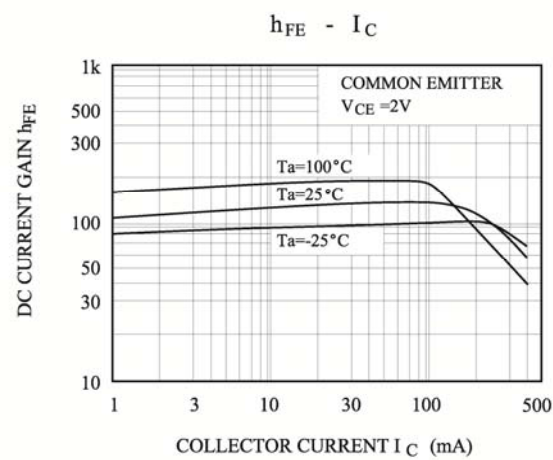
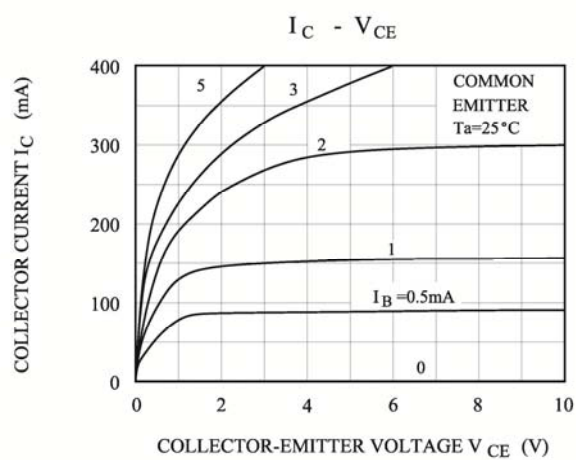
Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	80	V
Collector Emitter Voltage	V_{CEO}	80	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	400	mA
Base Current	I_B	80	mA
Total Power Dissipation	P_{tot}	0.5 1 ¹⁾	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

¹⁾ When mounted on a 250 mm² x 0.8 t ceramic substrate.

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at V _{CE} = 2 V, I _C = 50 mA	h _{FE} h _{FE} h _{FE}	70	-	140	-
Current Gain Group O		120	-	240	-
Y		50	-	-	-
at V _{CE} = 2 V, I _C = 200 mA					
Collector Base Cutoff Current at V _{CB} = 80 V	I _{CBO}	-	-	100	nA
Emitter Base Cutoff Current at V _{EB} = 5 V	I _{EBO}	-	-	100	nA
Collector Emitter Breakdown Voltage at I _C = 10 mA	V _{(BR)CEO}	80	-	-	V
Collector Emitter Saturation Voltage at I _C = 200mA, I _B = 20 mA	V _{CE(sat)}	-	-	0.4	V
Base Emitter Voltage at V _{CE} = 2 V, I _C = 5 mA	V _{BE(on)}	0.55	-	0.8	V
Transition Frequency at V _{CE} = 10 V, I _C = 10 mA	f _T	-	100	-	MHz
Collector Output Capacitance at V _{CB} = 10 V, f = 1 MHz	C _{ob}	-	10	-	pF





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Package Outline(Dimensions in mm)

SOT-89

